

Physics ECAT Pre Engineering Chapter 18 Electronics Physics Online Test

Sr	Questions	Answers Choice
1	In an N-type silicon, which of the following statement is true	A. Electrons are majority carriers and trivalent atoms are the dopants B. Electrons are minority carriers and pentavalent atoms are the dopants C. Holes are minority carriers and pentavalent atoms are the dopants D. Holes are majority carriers and trivalent atoms are the dopants
2	The value of LDR depends upon intensity of:	A. Sound falling on it B. Current passing through it C. Magnetic field surrounding it D. Light falling on it E. Non of these
3	A potential barrier of 0.7 V exists across p-n junction made from:	A. Germanium B. Silicon C. Arsenic D. Gallium E. Indium
4	If both the inputs given to a gate are 1 such that the output is 0, then it is:	A. AND gate B. NOR gate C. OR gate D. NOT gate E. Both (A) and (C)
5	In reverse-biased p-n junction, the reverse current is due to flow of:	A. Minority charge carriers B. Majority charge carriers C. Free electrons from p to n-region D. Holes from n to p-region E. all are true except (B)
6	Majority charge carriers in the p-region of p-n junction are:	A. electrons B. positrons C. Holes D. Neutrons E. None of these
7	In a transistor, collector current is controlled by	A. Collector voltage B. Base current C. Collector resistance D. All of the above
8	Depletion region contains:	A. Protons B. Positive ions C. Negative ions D. Both (B) and (C) E. Both (A) and (C)
9	Field lines are closer to each other in the region where the field is	A. Stronger B. Weaker C. Much weaker D. Absent E. None of these
10	Michael Faraday is known by his work on	A. Nuclear strong force B. Gravitational force C. Nuclear weak force D. Electric force E. None of these
11	A potential barrier of 0.7V exists across p-n junction made from:	A. Germanium B. Silicon C. Arsenic D. Gallium E. Indium
12	All the valence electrons present in a crystal of silicon are bound in their orbits by	A. Ionic bond B. covalent bond C. Molecular bond D. Both (A) and (B) E. Both (B) and (C)

13	The SI unit of charge is	B. Watt C. Coulomb D. Volt E. Joule
14	When transistors are used in digital circuits they usually operate in the	A. Active region B. Breakdown region C. Saturation and cutoff regions D. Linear region
15	In full wave rectification, simultaneous action is that:	A. Two diodes conduct and two do not. B. One diode conduct and three do not. C. Three diodes conduct and one does not. D. All the four diodes conduct E. None of these
16	A transistor has:	A. One region B. Two regions C. Three regions D. Four regions E. None is correct
17	Crystal of germanium or silicon in its pure form at absolute zero acts as:	A. A conductor B. A semiconductor C. an insulator D. Both (A) and (C) E. Both (A) and (B)
18	In the text book, the transistor amplifier circuit is a:	A. Common emitter circuit B. Common collector circuit C. Common base circuit D. Any of these E. None of these
19	Inverter is the name given to:	A. NOT gate B. OR gate C. NOR gate D. AND gate E. XOR gate
20	A digital system deals with quantities which has discrete values:	A. Two in number B. One in number C. Three in number D. Four in number E. None of these
21	The number of input terminals of an op-amp is:	A. One B. Two C. Three D. Four E. None of these
22	If the distance between two charges is doubled, the force between them will become	A. Double B. Half C. Three times D. One fourth E. One third
23	A hole in p-type may be due to:	A. Trivalent impurity B. Breking of some covalent bond C. Pentavalent impurity D. Germanium E. Either (A) or (B)
24	The electric field lines start from	A. Positive charge B. Negative charge C. Either A or B D. Neutron E. An atom
25	Whenever a covalent bond breaks, it creates:	A. An electron B. A hole C. An electron-hole pair D. A positron E. All of these
26	Electric intensity at a place due to a charged conductor is a	A. Scalar quantity B. Vector quantity C. Semi vector and semi scalar D. Dimensionless quantity E. Both A and D are true
27	Improper biasing of a transistor circuit produces	A. Heavy loading of emitter current B. Distortion in the output signal C. Excessive heat at collector terminal D. Faulty location of load line

		D. Faulty location of load line
28	To make an LED, it is impracticable to use:	A. Silicon B. Gallium arsenide C. Gallium arsenide phosphide D. Iron E. Both (B) and (C)
29	The use of chips in electrons is described in the form of:	A. Yellow boxes B. Black boxes C. Red boxes D. White boxes E. Orange boxes
30	To turn the transistor OFF, the base current is set:	A. At maximum value B. At zero C. Either (A) or (B) D. All are correct E. None of correct
31	Electric field strength is defined as	A. Work done on unit charge B. Force exerted on unit charge C. Distance covered by unit charge D. Power exerted by unit charge E. None of these
32	The values 1 and 0 are designated as:	A. Continuous values B. Binary values C. Boolean values D. Decimal values E. Either (B) and (C)
33	To display a digit of EIGHT, the number of ON LED'S are:	A. Two B. Three C. Five D. Seven E. Eight
34	Computer chips are made from:	A. Iron B. Silicon C. Helium D. Stontium E. Aluminium
35	Op-amp has been discussed as comparator of:	A. Distances B. Voltages C. Velocities D. Magnetic fields E. Both (A) and (C)
36	The value of relative permittivity of different dielectrics are	A. Equal B. Different C. Greater than one D. Smaller than one E. Both B and C
37	The reverse saturation current in a PN junction diode is only due to	A. Majority carriers B. Minority Carriers C. Acceptor ions D. Donor ions
38	Origin of the electric and the gravitational forces	A. Was known in 1911 A.D. B. Was known in 1811 A.D. C. Was known in 1711 A.D. D. is still unknown E. Was known in 1611 A.D.
39	Most of the electrons in the base of an NPN transistor flow	A. Out of the base lead B. Into the collector C. Into the emit D. Into the base supply
40	An LED emits light when it is:	A. Forward biased B. Reverse biased C. Operated without battery D. Operated with heat source E. None of these
41	By placing a dielectric in between the charges, the electrostatic force between them	A. Is always reduced B. Is always increased C. Is not affected D. Is increased one million times E. None of these
42	Conversion of A.C. into D.C. is called:	A. Rectification B. Amplification C. Electric induction D. Magnetic induction E. None of these

43	In AND gate, the output is 1 if:	A. Both inputs are 0 B. Both inputs are 1 C. Only one input is 0 D. Both (A) and (B) E. Both (A) and (C)
44	The number of LED'S needed to display all the digits is:	A. Four B. Five C. Nine D. Six E. Seven
45	To designate the voltage as low or 0 by a logic gate, the specified minimum value is:	A. 0.2 volt B. 0.8 volt C. 0 volt D. 2.0 volt E. 5.0 volt
46	An electronic computer is basically a vast arrangement of electronic switches which are made from	A. Resistors B. Transistors C. N -type crystals D. P-Type crystals E. Capacitors
47	In describing function of digital systems, 1 represents:	A. Closed switch B. True Statement C. Lighted bulb D. Only (B) and (C) E. All are true
48	Silicon is one of the mot commonly used:	A. onductor B. Dielectric C. Insulator D. Semiconduction E. Both (B) and (C)
49	The concept of electric field theory was introduced by	A. Michael Faraday B. Newton C. Dalton D. Kepler E. Einstein
50	Electric lines of force	A. Intersect each other B. Are always parallel C. Are always anti-parallel D. Never intersect E. None of these
51	Electric field lines emerge from the charges in	A. One dimension B. Two dimensions C. Three dimensions D. Four dimensions E. None of these
52	.Depletion region contains:	A. Protons B. Positive ions C. Negative ions D. Both (B) and (C) E. Both (A) and (C)
53	Truth table of logic function:	A. Summarizes its output values B. Tabulates all its input conditions only C. Display all its input/output possibilities D. Is not based on logic algebra E. None of these
54	A diode which can turn its current ON and OFF in nono seconds is called:	A. LED B. Photodiode C. An ordinary diode. D. Both (A) and (B) E. Both (B) and (C)
55	The intensity at a point due to a charge is inversely proportional to	A. Amount of charge B. Size of the charge C. Distance between charge and the point D. Square of the distance from the charge E. None of these
56	In the forward biases situation, the current flowing across the p-n junction is a few:	A. amperes B. Milli amperes C. Micro amperes D. Pico amperes E. None of these

